

SWXFT100CPM

900V SiC Power Module Common Source Bi-Directional Blocking

Features

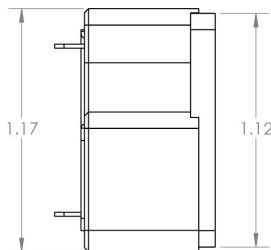
- Ultra-low ON resistance
- Bi-directional Blocking
- High Fault Tolerance
- High Power Density

Applications

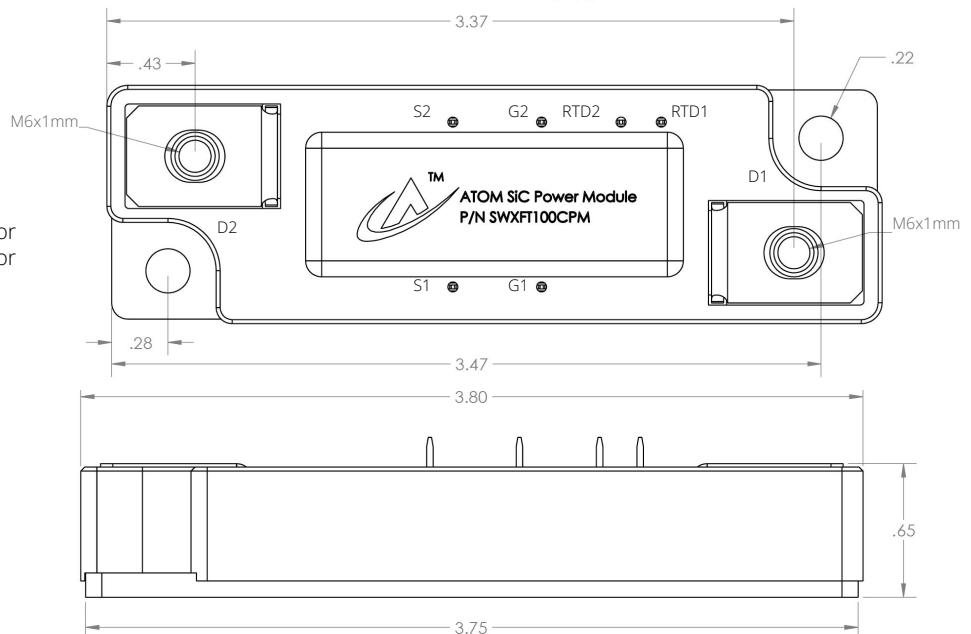
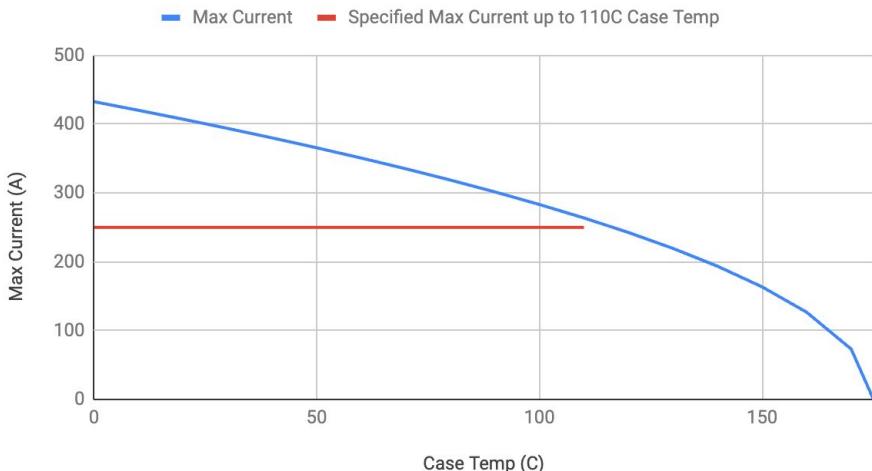
- Solid-State Circuit Breakers
- Circuit Protection Devices
- Static Transfer Switches
- Islanding Devices

Pin Layout Key:

D1 = Drain 1 connection
 D2 = Drain 2 connection
 G1 = Gate 1
 G2 = Gate 2
 RTD1 = Baseplate resistance temperature detector
 RTD2 = Baseplate resistance temperature detector
 S1 = Source 1
 S2 = Source 2



Max Current vs. Case Temperature



UL File No: E502103

Performance Data

Maximum Ratings (T_j=25°C unless otherwise specified)

| Item | Symbol | Unit | Value | Conditions |
|--|-----------------------|------|-------|---|
| Drain-Drain voltage | VDD | V | 900 | |
| Gate-source voltage(+) | VGSS(+) | V | 15 | Static |
| Gate-source voltage(-) | VGSS(-) | V | -4 | Static |
| Gate-source voltage(+) | VGSS(+) | V | 19 | Dynamic |
| Gate-source voltage(-) | VGSS(-) | V | -8 | Dynamic |
| Continuous drain to drain current | IDD | A | 250 | T _c =110°C |
| Pulsed drain current | IDRM | A | 1800 | Pulse width limited by T _j (max) |
| Total power dissipation | Ptot | W | 600 | T _c =110°C |
| Junction temperature T _j (max) oC | T _j (maxx) | C | 175 | |
| Storage temperature T _{stg} oC | T _{stg} | C | 125 | |
| Isolation voltage | Viso | V | 2500 | AC 60Hz 1 min |

Electrical Characteristics (T_j=25°C unless otherwise specified)

| Item | Symbol | Unit | Min. | Typ. | Max | |
|-------------------------------------|---------|-------|------|------|------|---|
| Drain-Drain breakdown voltage | V(BR)DD | V | 900 | | | VGS=0V, ID=400uA |
| Static drain-drain on-state voltage | VDS(on) | | | 2.2 | | VGS=15V, ID= 250 A, T _j =175°C |
| On state resistance | RDS(on) | mOhms | | 6.0 | 6.5 | VGS=15V, ID= 250A, T _j =25C |
| | RDS(on) | mOhms | | 8.5 | 9.0 | VGS=15V, ID= 250A, T _j =175C |
| Drain-source leakage current | IDSS | uA | | 4 | 400 | VDS=900V VGS= 0V |
| Gate-source threshold voltage | VGS(th) | V | 1.7 | 2.4 | 3.5 | VDS=VGS, ID=33mA, T _j =25C |
| | VGS(th) | V | | 1.7 | | VDS=VGS, ID=33mA, T _j =175C |
| Gate-source leakage current | IGSS | nA | | 40 | 1000 | VGS=15, VDS=0 |

Thermal Characteristics

| Item | Symbol | Unit | Min. | Typ. | Max |
|---|--------|------|------|----------|-----|
| Junction-to-case thermal resistance R _{th(j-c)} | | | | 0.09 C/W | |

Additional Module Data

| Item | Symbol | Unit | Min. | Typ. | Max |
|-----------------------|--------|-------|------|------|-----|
| Weight | Wt | g | | 120 | |
| Mounting torque | | in-lb | | 24 | |
| Power Terminal torque | | in-lb | | 24 | |

Electrical Ratings of the Thermistor

| | | | | |
|--|---------|--------|-------|------|
| Calibration class number | C4 | | | |
| Resistance R ₂₅ | 1K ohm | +/- 5% | at 25 | ±2°C |
| Temperature - max operating ambient | 150C | | | |
| The value that is twice R _{min} | 200 ohm | | | |